





#### **500V PNP HIGH VOLTAGE TRANSISTOR IN SOT223**

#### **Features**

- BV<sub>CEO</sub> > -500V
- I<sub>C</sub> = -150mA High Continuous Current
- I<sub>CM</sub> = -500mA Peak Pulse Current
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

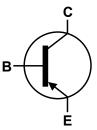
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>@3</a>
- · Weight: 0.112 grams (approximate)

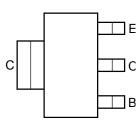




Top View



Device Symbol



Top View Pin-Out

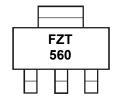
#### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT560TA	AEC-Q101	FZT560	7	12	1,000
FZT560QTA	Automotive	FZT560	7	12	1,000
FZT560TC	AEC-Q101	FZT560	13	12	4,000
FZT560QTC	Automotive	FZT560	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**



FZT560 = Product Type Marking Code





### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-500	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-500	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-150	mA
Peak Pulse Current	I <sub>CM</sub>	-500	mA

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	D-	2	W
Power Dissipation	(Note 7)	$P_{D}$	3	W
Thermal Resistance, Junction to Ambient	(Note 6)	Б	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{\theta JL}$	14.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 9)

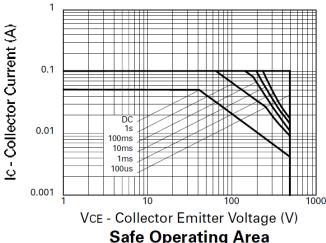
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

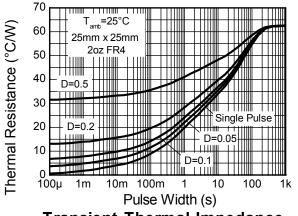
- 6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air For a device mounted with the collector lead on 25mm x 25mm x02 copper that is conditions whilst operating in steady-state.
  Same as note (6), except the device is mounted on 50mm x 50mm 2oz copper.
  Thermal resistance from junction to solder-point (at the end of the collector lead).
  Refer to JEDEC specification JESD22-A114 and JESD22-A115.



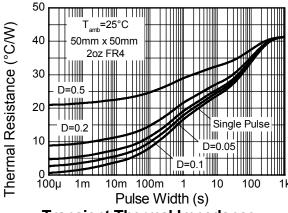
## **Thermal Characteristics and Derating Information**



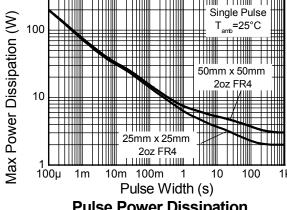
## Safe Operating Area



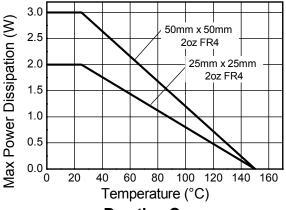
**Transient Thermal Impedance** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 





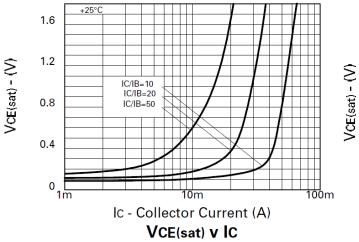
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

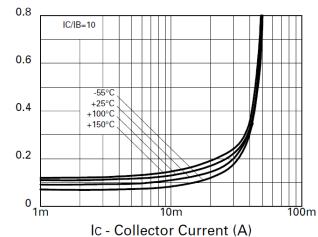
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-500	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-500	_	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	$I_E = -100 \mu A$
Collector Cut-off Current	I <sub>CBO</sub>	-	_	-100	nA	V <sub>CB</sub> = -500V
Collector Cut-off Current	I <sub>CES</sub>	-	_	-100	nA	V <sub>CE</sub> = -500V
Emitter Cut-off Current	I <sub>EBO</sub>	-	_	-100	nA	V <sub>EB</sub> = -5.6V
Collector Emitter Seturation Voltage (Note 10)	V	-	-	-200	mV	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	-	_	-500	IIIV	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	-	-900	mV	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	-	_	-900	mV	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$
		100	_	300		$I_C = -1 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain (Note 10)	h <sub>FE</sub>	80	_	300	_	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$
, ,		_	15	_		I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V
Current Gain-Bandwidth Product	f <sub>T</sub>	60	-	-	MHz	$V_{CE} = -20V, I_{C} = -10mA$ f = 50MHz
Turn-On Time	t <sub>on</sub>	_	110	_	ns	V <sub>CC</sub> = -100V, I <sub>C</sub> = -50mA
Turn-Off Time	t <sub>off</sub>	_	1.5	_	μs	$I_{B1} = -5mA$ , $I_{B2} = 10mA$
Output Capacitance	$C_obo$	_	_	8	pF	V <sub>CB</sub> = -20V, f = 1MHz

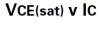
Notes: 10. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%

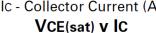


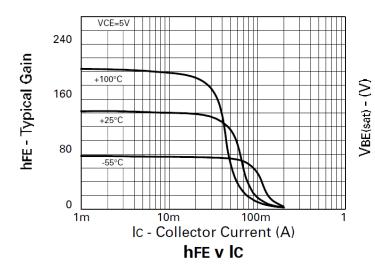
# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

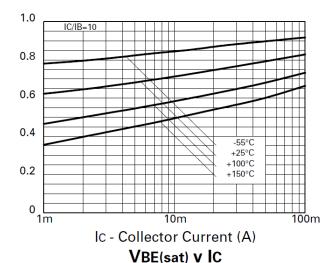


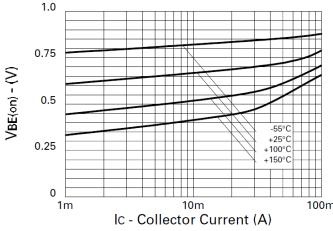








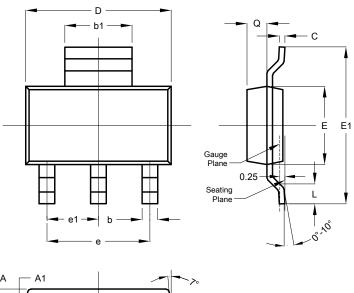




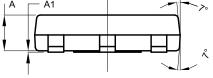


## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

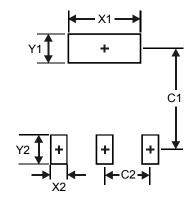


SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
X1	3.3		
X2	1.2		
Y1	1.6		
Y2	1.6		
C1	6.4		
C2	2.3		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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